

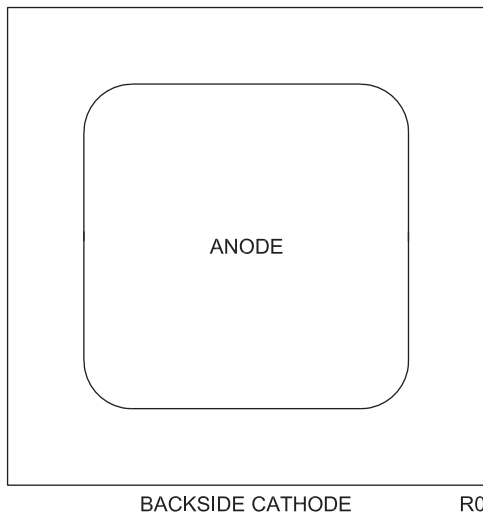
**PROCESS CPD05**  
**General Purpose Rectifier**  
1 Amp Glass Passivated Rectifier Chip



**PROCESS DETAILS**

Process	GLASS PASSIVATED MESA
Die Size	51 x 51 MILS
Die Thickness	10.2 MILS
Anode Bonding Pad Area	36 x 36 MILS
Top Side Metalization	Ni/Au - 5,000Å/2,000Å
Back Side Metalization	Ni/Au - 5,000Å/2,000Å

**GEOMETRY**



**GROSS DIE PER 4 INCH WAFER**

4,250

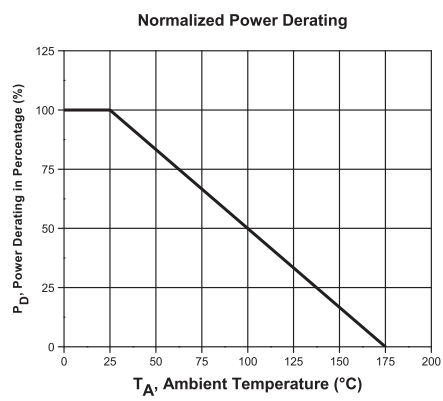
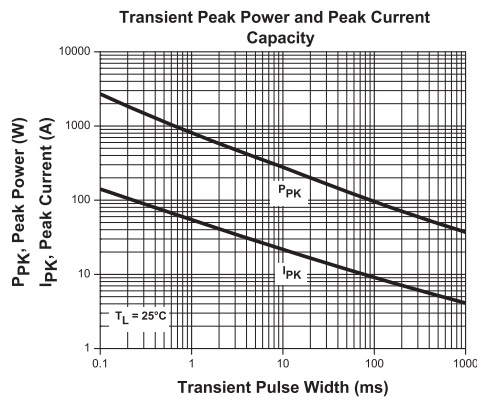
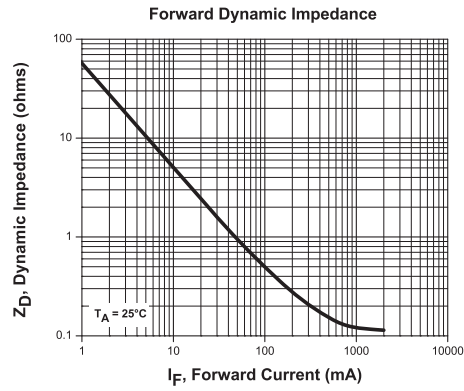
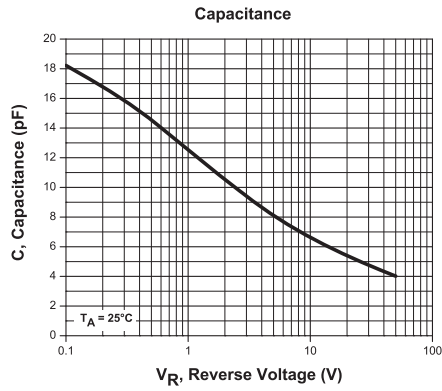
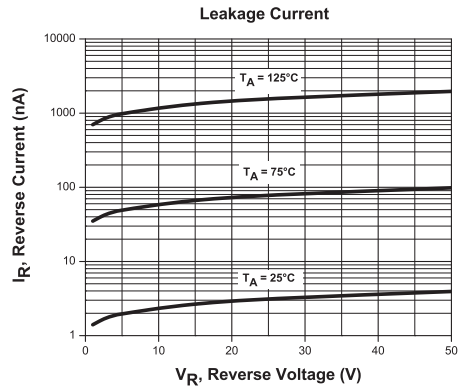
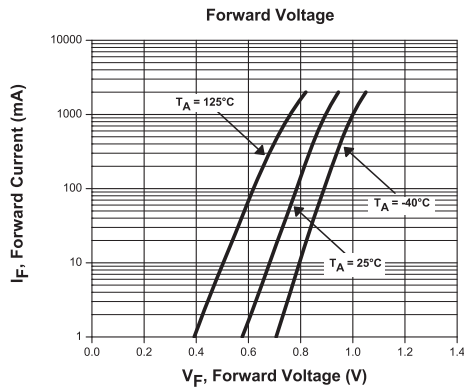
**PRINCIPAL DEVICE TYPES**

1N3611 thru 1N3614  
1N4001 thru 1N4007  
1N4245 thru 1N4249  
1N5059 thru 1N5062  
1N5391 thru 1N5399  
1N5614 thru 1N5622  
CMR1-02 Series  
CMR1-02M Series

R4 (22-March 2010)

# PROCESS CPD05

## Typical Electrical Characteristics



R4 (22-March 2010)